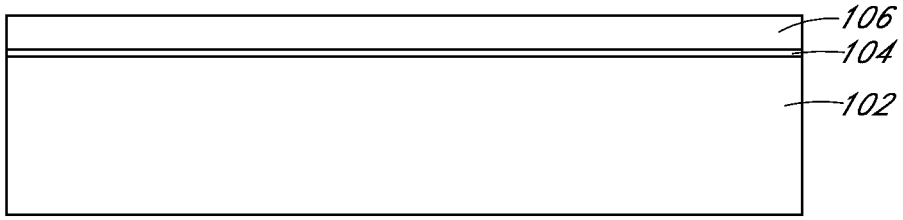

FIG. 1A

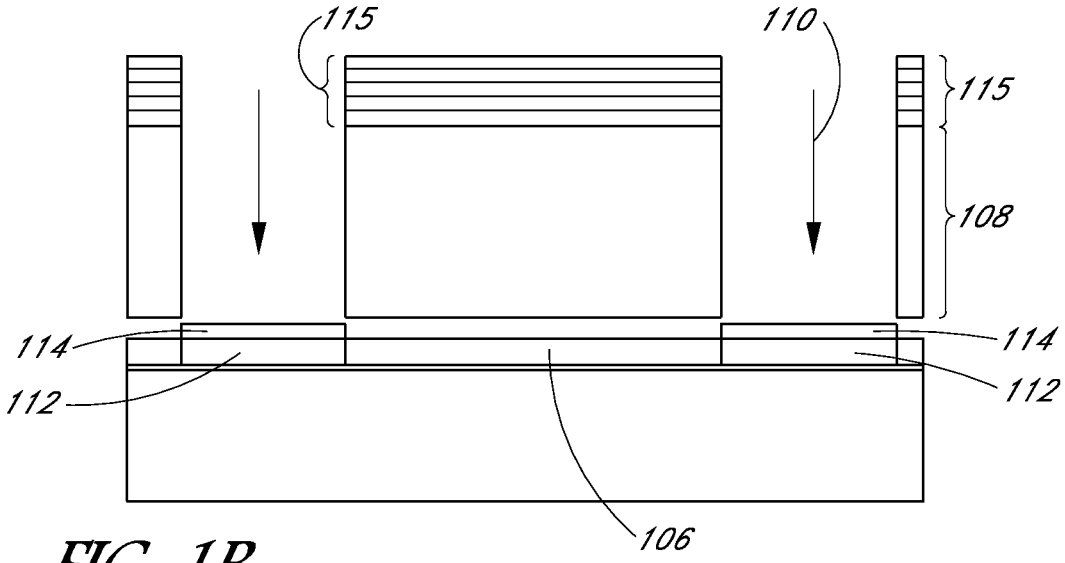

FIG. 1B

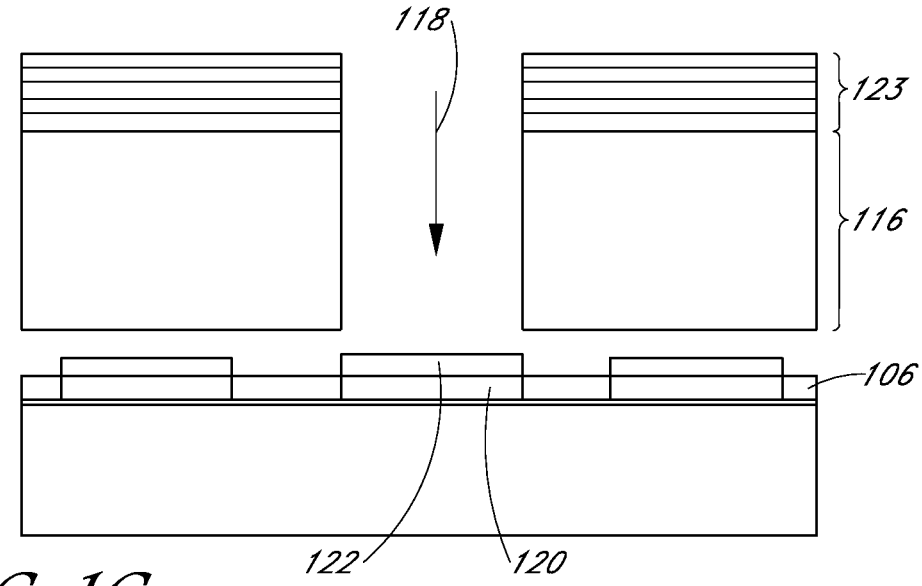

FIG. 1C

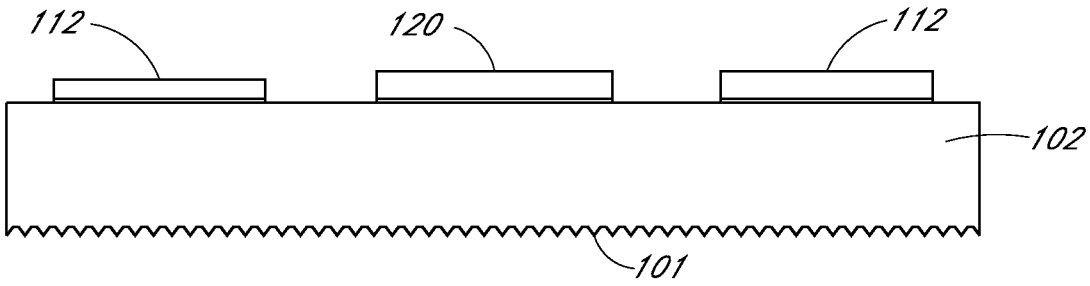

FIG. 1D

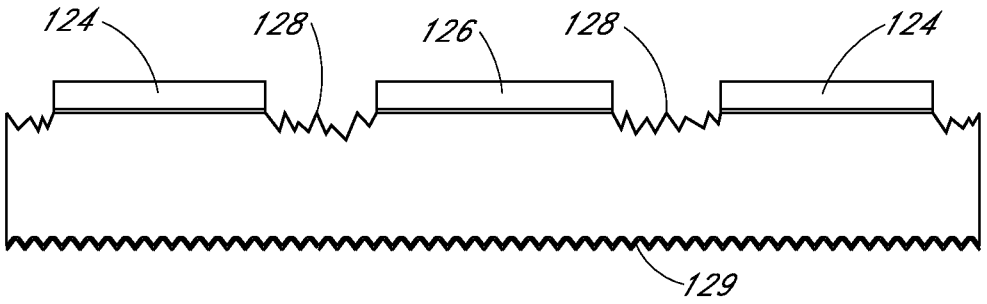

FIG. 1E

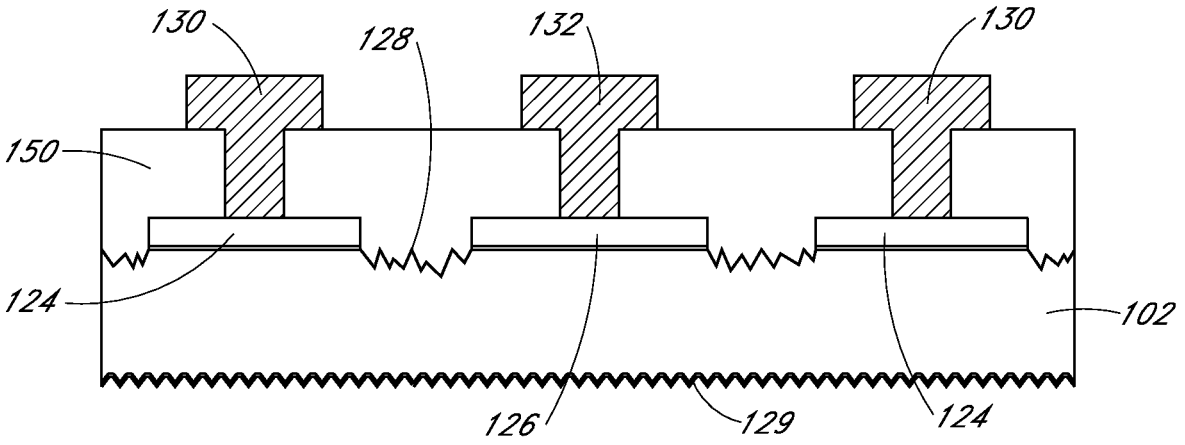

FIG. 1F

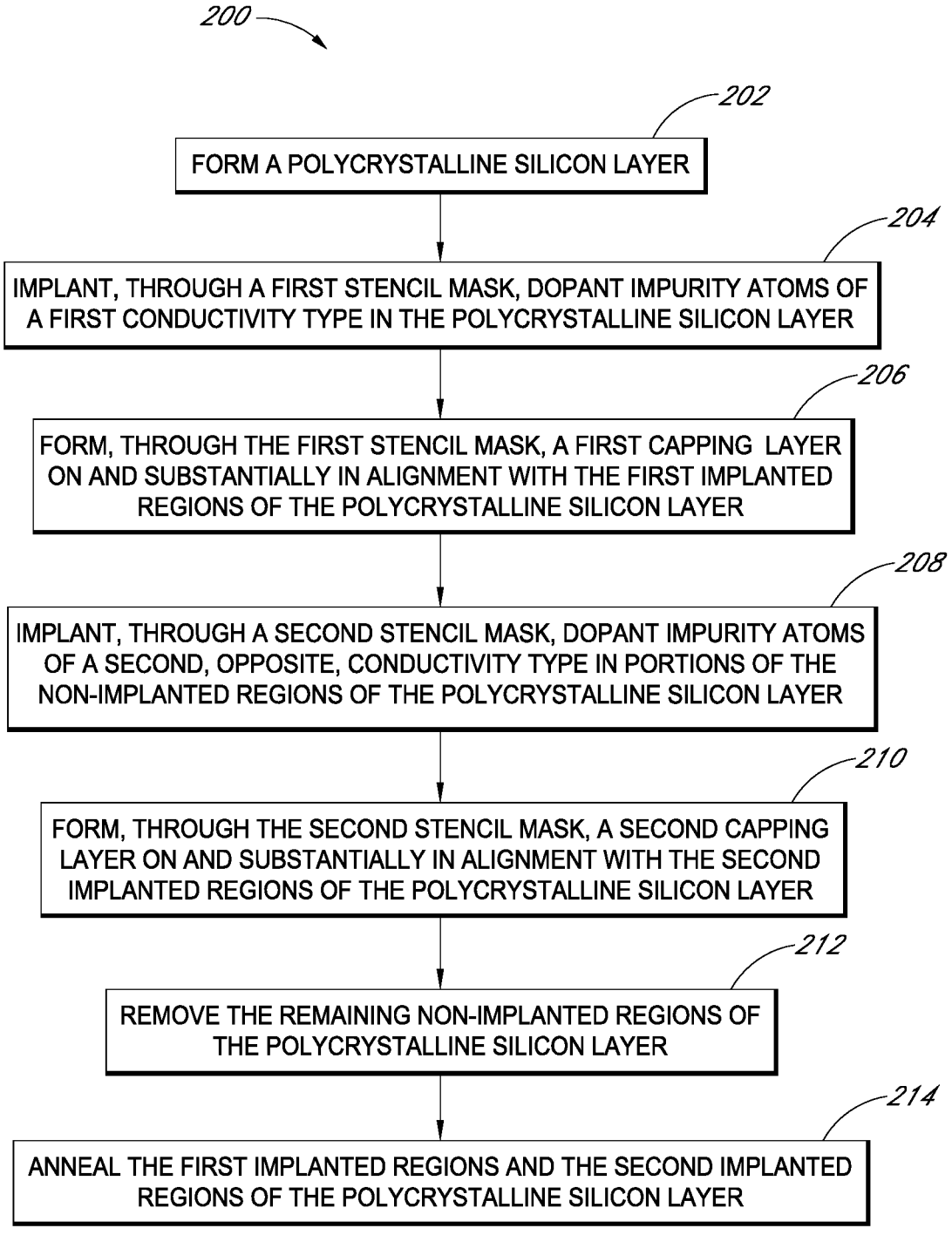
200
202
FORM A POLYCRYSTALLINE SILICON LAYER
204
IMPLANT, THROUGH A FIRST STENCIL MASK, DOPANT IMPURITY ATOMS OF A FIRST CONDUCTIVITY TYPE IN THE POLYCRYSTALLINE SILICON LAYER
206
FORM, THROUGH THE FIRST STENCIL MASK, A FIRST CAPPING LAYER ON AND SUBSTANTIALLY IN ALIGNMENT WITH THE FIRST IMPLANTED REGIONS OF THE POLYCRYSTALLINE SILICON LAYER
208
IMPLANT, THROUGH A SECOND STENCIL MASK, DOPANT IMPURITY ATOMS OF A SECOND, OPPOSITE, CONDUCTIVITY TYPE IN PORTIONS OF THE NON-IMPLANTED REGIONS OF THE POLYCRYSTALLINE SILICON LAYER
210
FORM, THROUGH THE SECOND STENCIL MASK, A SECOND CAPPING LAYER ON AND SUBSTANTIALLY IN ALIGNMENT WITH THE SECOND IMPLANTED REGIONS OF THE POLYCRYSTALLINE SILICON LAYER
212
REMOVE THE REMAINING NON-IMPLANTED REGIONS OF THE POLYCRYSTALLINE SILICON LAYER
214
ANNEAL THE FIRST IMPLANTED REGIONS AND THE SECOND IMPLANTED REGIONS OF THE POLYCRYSTALLINE SILICON LAYER

FIG. 2

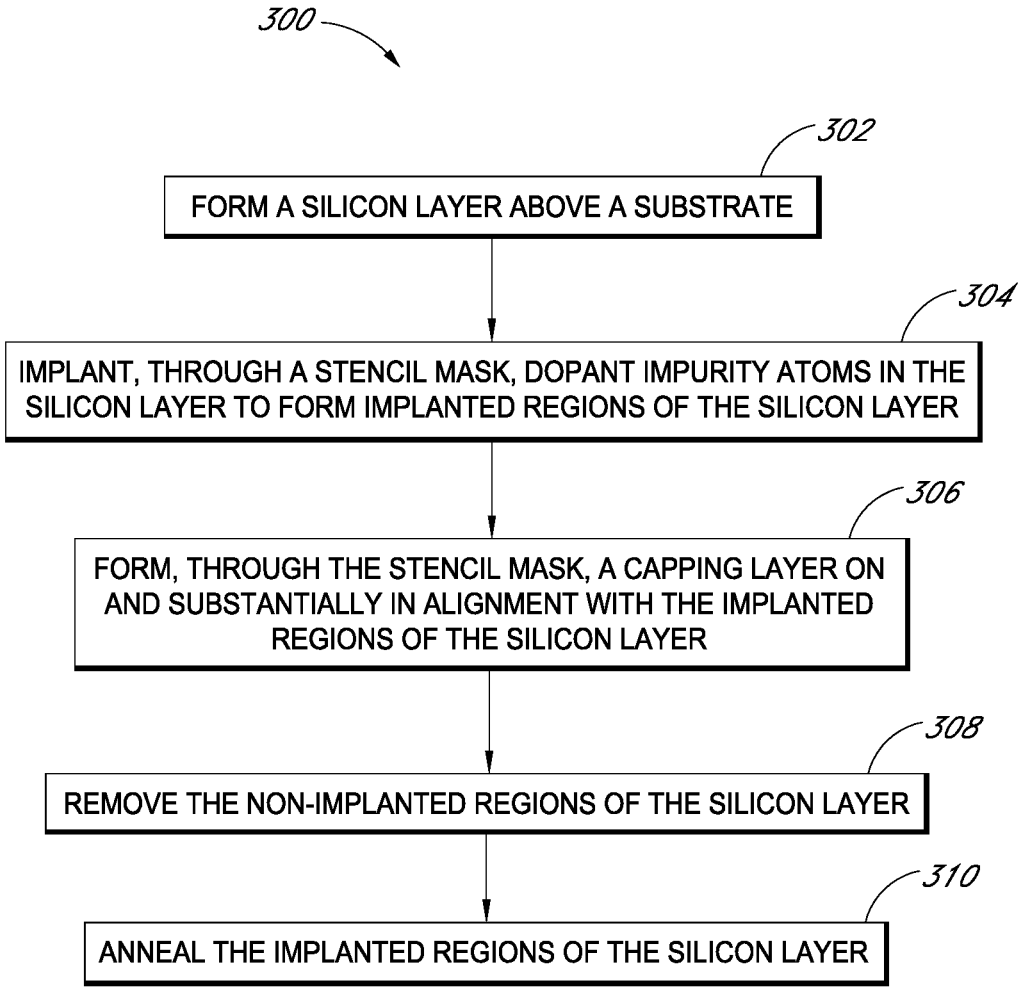
300
302
FORM A SILICON LAYER ABOVE A SUBSTRATE
304
IMPLANT, THROUGH A STENCIL MASK, DOPANT IMPURITY ATOMS IN THE SILICON LAYER TO FORM IMPLANTED REGIONS OF THE SILICON LAYER
306
FORM, THROUGH THE STENCIL MASK, A CAPPING LAYER ON AND SUBSTANTIALLY IN ALIGNMENT WITH THE IMPLANTED REGIONS OF THE SILICON LAYER
308
REMOVE THE NON-IMPLANTED REGIONS OF THE SILICON LAYER
310
ANNEAL THE IMPLANTED REGIONS OF THE SILICON LAYER

FIG. 3

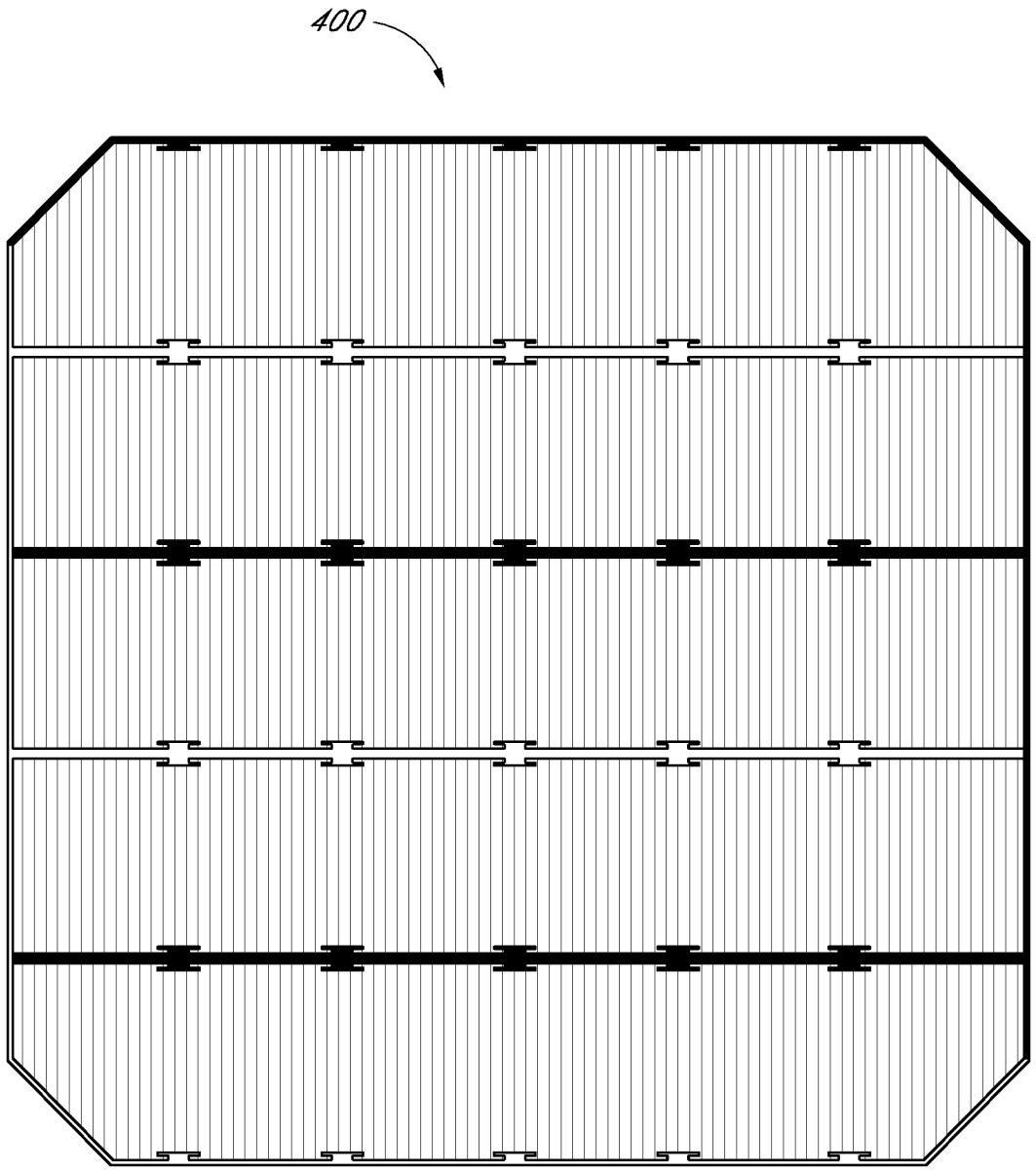

FIG. 4

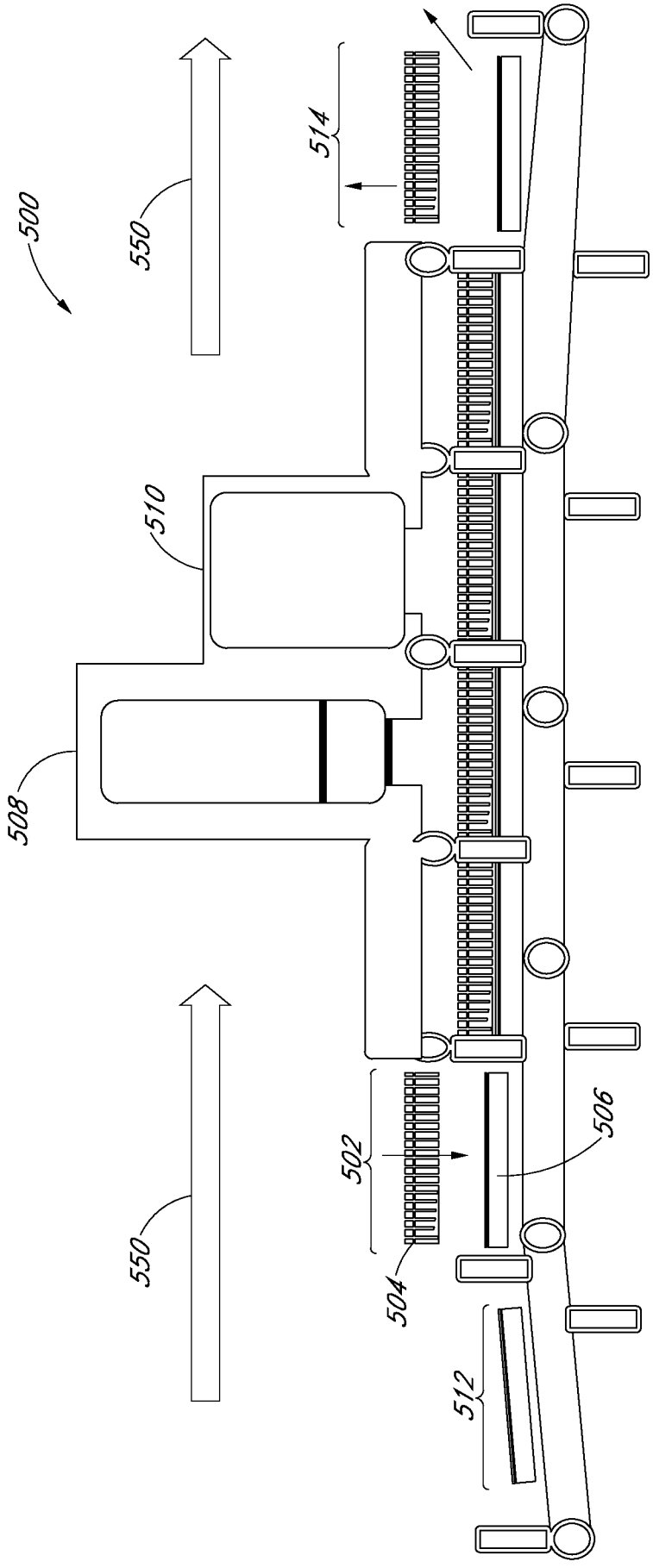

FIG. 5A

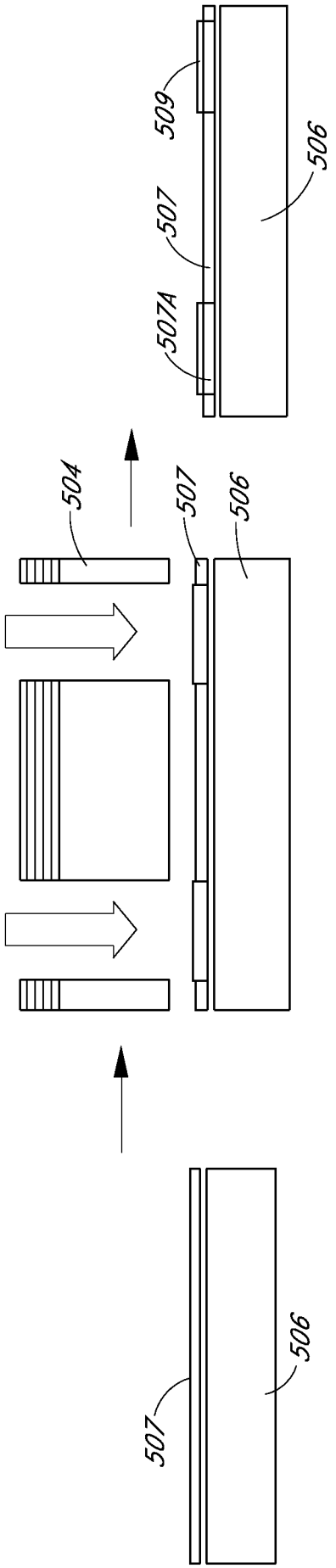

FIG. 5B

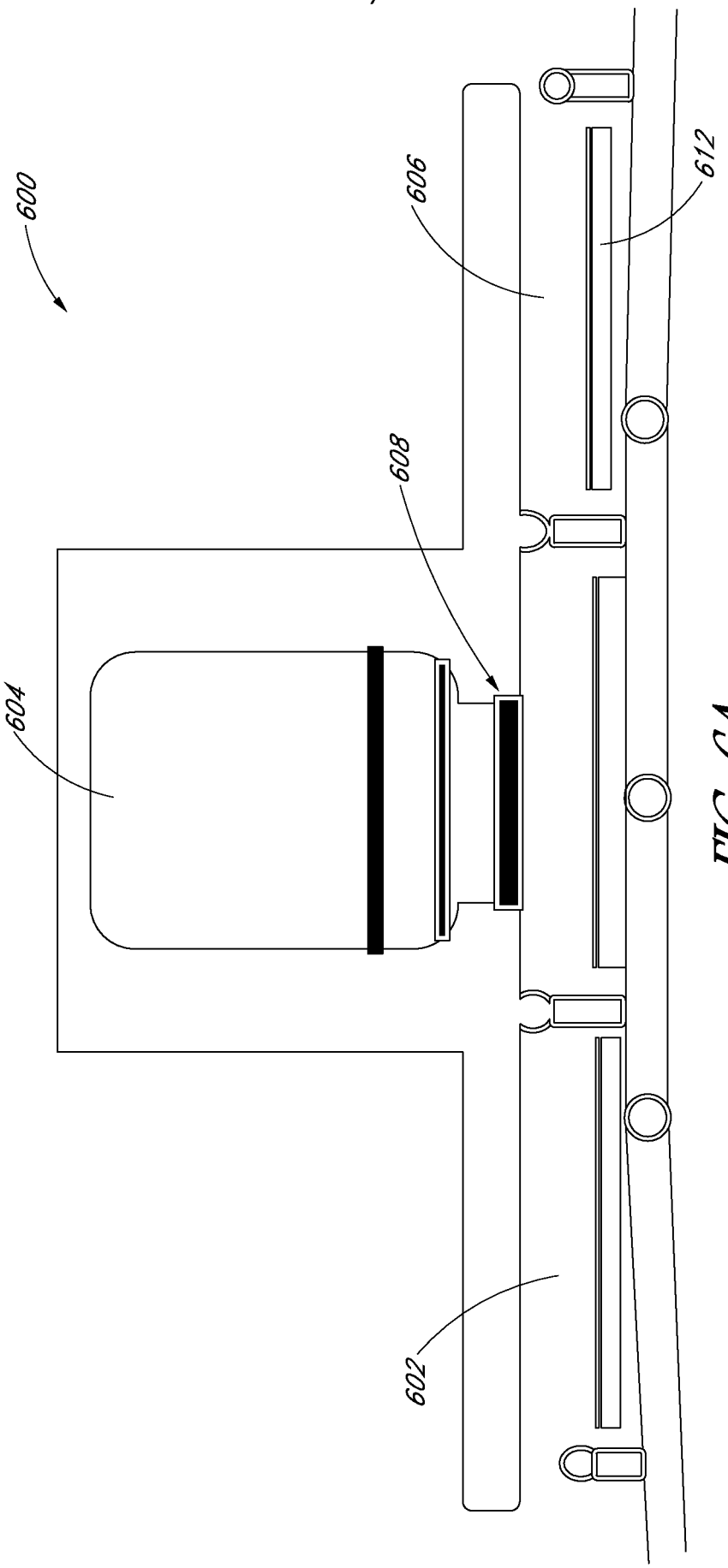

FIG. 6A

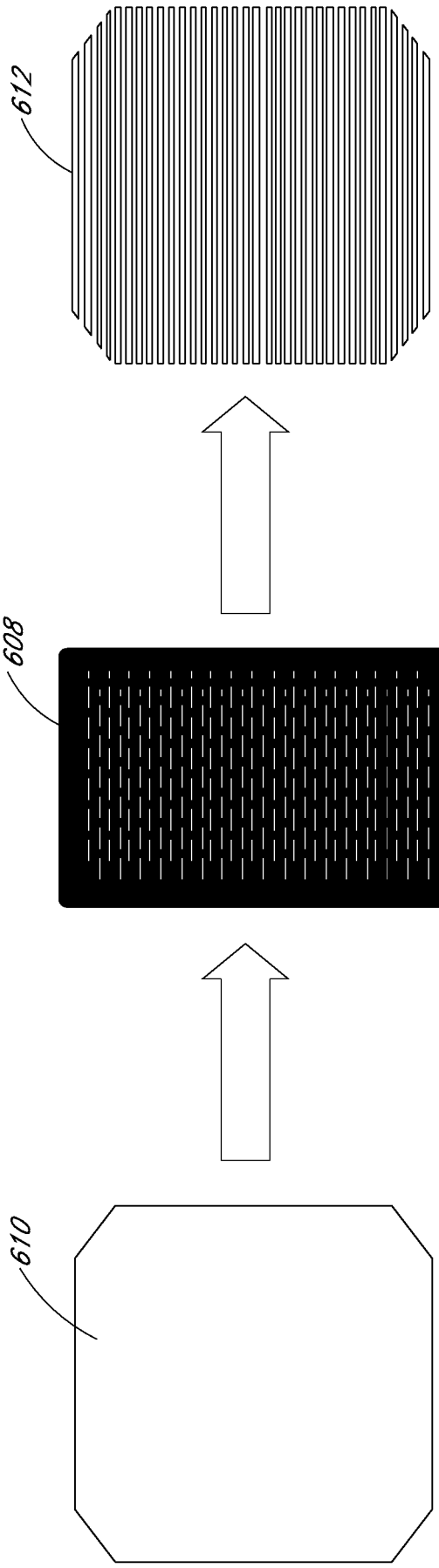

FIG. 6B

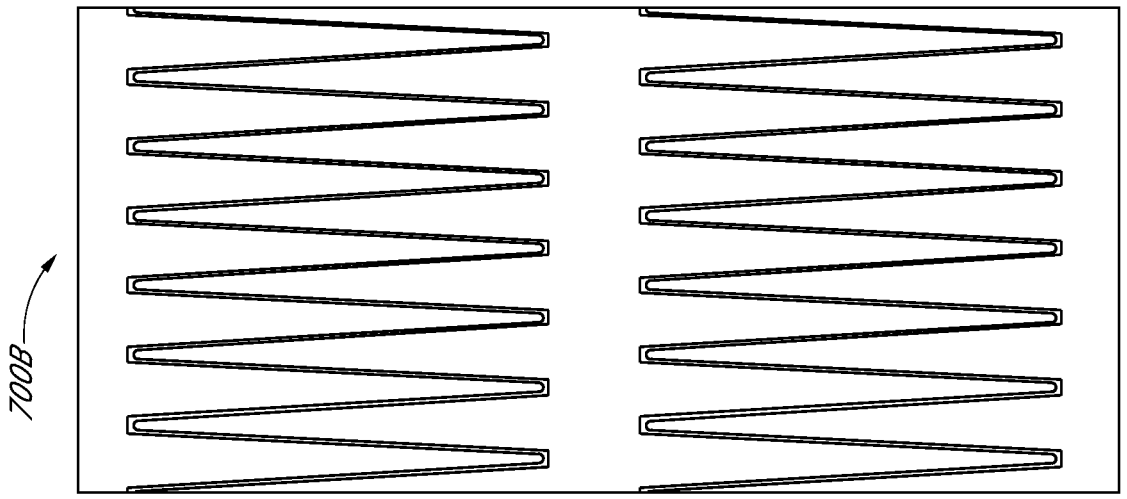

FIG. 7B

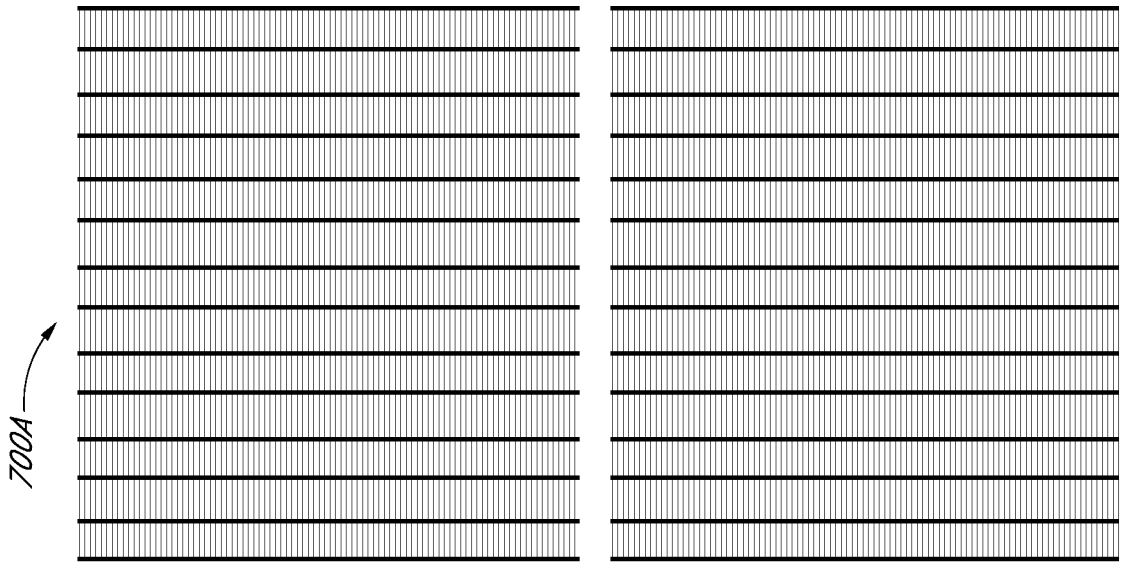

FIG. 7A

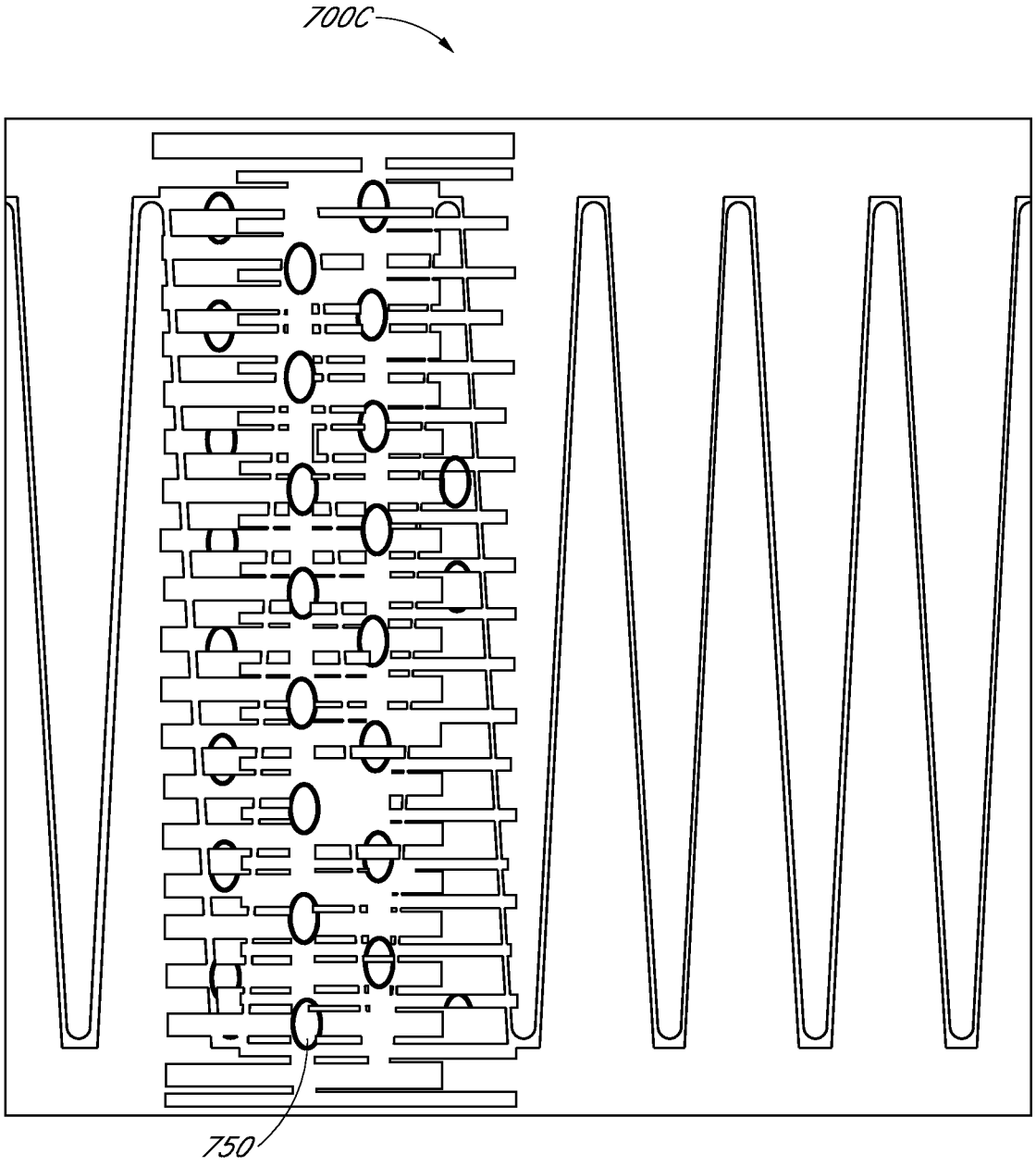

FIG. 7C